

IN THE CLAIMS

Please amend the claims as follows:

1-27 (Canceled).

28 (Original): A crystallization apparatus which comprises an illumination system which illuminates a phase shifter, and irradiates a polycrystal semiconductor film or an amorphous semiconductor film with a light beam having a predetermined light intensity distribution through the phase shifter, thereby generating a crystallized semiconductor film,

wherein the phase shifter has a first phase shift line which linearly extends along a predetermined direction and a second phase shift line which is continuous with the first phase shift line and meanders along the predetermined direction.

29 (Original): A crystallization apparatus which comprises an illumination system which illuminates a phase shifter, and irradiates a polycrystal semiconductor film or an amorphous semiconductor film with a light beam having a predetermined light intensity distribution through the phase shifter, thereby generating a crystallized semiconductor film,

wherein the phase shifter has a first phase shift line which meanders with a first shaped width along a predetermined direction and a second phase shift line which is continuous with the first phase shift line and meanders with a second shaped width substantially larger than the first shaped width along the predetermined width.

30 (Original): The crystallization apparatus according to claim 28, wherein areas defining with the first phase shift line and the second phase shift line therebetween have a phase difference of approximately 180 degrees.

31 (Original): A crystallization apparatus which comprises an illumination system which illuminates a phase shifter, and irradiates a polycrystal semiconductor film or an amorphous semiconductor film with a light beam having a predetermined light intensity distribution through the phase shifter, thereby generating a crystallized semiconductor film, wherein the phase shifter has a first phase shift line which linearly extends along a predetermined direction, a second phase shift line which meanders along the predetermined direction and a third phase shift line which linearly extends and crosses the first phase shift line.

32 (Original): The crystallization apparatus according to claim 31, wherein an area on one side and an area on the other side of the first phase shift line and the second phase shift line have a phase difference of approximately 180 degrees, and an area on one side and an area on the other side of the third phase shift line have a phase difference of approximately 180 degrees.

33 (Original): The crystallization apparatus according to claim 31, wherein the first phase shift line and the third phase shift line are substantially orthogonal to each other.

34 (Original): The crystallization apparatus according to claim 28, wherein the polycrystal semiconductor film or the amorphous semiconductor film and the phase shifter are arranged in substantially parallel with and in close proximity to each other.

35 (Original): The crystallization apparatus according to claim 34, wherein assuming that  $\lambda$  is a wavelength of the light and D is a distance between the polycrystal semiconductor

film or the amorphous semiconductor film and the phase shifter, the shaped width W of the second phase shift line satisfies the following condition:

$$W > 0.6 \times (\lambda D/2)^{1/2}$$

36 (Original): The crystallization apparatus according to claim 28 further comprising an image forming optical system which is arranged in a light path between the polycrystal semiconductor film or the amorphous semiconductor film and the phase shifter,

wherein the polycrystal semiconductor film or the amorphous semiconductor film is set apart from a surface optical conjugate with the phase shifter by a predetermined distance along an optical axis of the image forming optical system.

37 (Original): The crystallization apparatus according to claim 28 further comprising an image forming optical system which is arranged in a light path between the polycrystal semiconductor film or the amorphous semiconductor film and the phase shifter,

wherein the polycrystal semiconductor film or the amorphous semiconductor film is set to a surface optically substantially conjugate with the phase shifter, and

an image side numerical aperture of the image forming optical system is set to a necessary value used to generate the predetermined light intensity distribution.

38 (Original): The crystallization apparatus according to claim 37, wherein assuming that  $\lambda$  is a wavelength of the light and NA is an image side numerical aperture of the image forming optical system, the shaped width W of the second phase shift line satisfies the following condition:

$$W > 0.305 \times \lambda/NA$$

39 (Original): A crystallization method which illuminates a phase shifter and irradiates a polycrystal semiconductor film or an amorphous semiconductor film with a light beam having a predetermined light intensity distribution through the phase shifter, thereby generating a crystallized semiconductor film,

the method using a phase shifter having a first phase shift line which linearly extends along a predetermined direction and a second phase shift line which is continuous with the first phase shift line and meanders along the predetermined direction.

40 (Original): A crystallization method which illuminates a phase shifter and irradiates a polycrystal semiconductor film or an amorphous semiconductor film with a light beam having a predetermined light intensity distribution through the phase shifter, thereby generating a crystallized semiconductor film

the method using a phase shifter having a first phase shift line which meanders with a first shaped width along a predetermined direction and a second phase shift line which is continuous with the first phase shift line and meanders with a second shaped width substantially larger than the first shaped width along the predetermined direction.

41 (Original): A crystallization method which illuminates a phase shifter and irradiates a polycrystal semiconductor film or an amorphous semiconductor film with a light beam having a predetermined light intensity distribution through the phase shifter, thereby generating a crystallized semiconductor film,

the method using a phase shifter having a first phase shift line which linearly extends along a predetermined direction, a second phase shift line which is continuous with the first phase shift line and meanders along the predetermined direction, and a third phase shift line which linearly extends and crosses the first phase shift line.

42 (Original): The crystallization method according to claim 39, wherein the polycrystal semiconductor film or the amorphous semiconductor film and the phase shifter are arranged in substantially parallel with and in close proximity to each other.

43 (Original): The crystallization method according to claim 39, wherein an image forming optical system is arranged in a light path between the polycrystal semiconductor film or the amorphous semiconductor film and the phase shifter, and

a surface of the polycrystal semiconductor film or the amorphous semiconductor film is set apart from a surface optically conjugate with the phase shifter by a predetermined distance along an optical axis of the image forming optical system.

44 (Original): The crystallization method according to claim 39, wherein an image forming optical system is arranged in a light path between the polycrystal semiconductor film or the amorphous semiconductor film and the phase shifter,

an image side numerical aperture of the image forming optical system is set to a necessary value used to generate the predetermined light intensity distribution, and

the polycrystal semiconductor film or the amorphous semiconductor film is set at a position optically conjugate with the phase shifter through the image forming optical system.

45 (Original): A crystallization method, wherein a phase shifter having a first phase shift line which extends along one direction and a second phase shift line which is continuous with the first phase shift line, extends in the one direction and meanders is used to modulate an incident light beam into a light beam having a light intensity distribution with an inverse peak pattern, a semiconductor film is irradiated with the modulated light, a crystal growth

start point is formed at a position corresponding to the first phase shift line, and a crystal is grown along the second phase shift line from the crystal growth start point.

46 (Original): A phase shifter having a first phase shift line which linearly extends along a predetermined direction and a second phase shift line which is continuous with the first phase shift line and meanders along the predetermined direction.

47 (Original): A phase shifter having a first phase shift line which meanders with a first shaped width along a predetermined direction and a second phase shift line which meanders with a second shaped width substantially larger than the first shaped width along the predetermined direction.

48 (Original): The phase shifter according to claim 46 having a plurality of areas which define the first phase shift line and the second phase shift line therebetween, wherein the adjacent areas have a phase difference of approximately 180 degrees.

49 (Original): A phase shifter having a first phase shift line which linearly extends along a predetermined direction, a second phase shift line which is continuous with the first phase shift line and meanders along the predetermined direction, and a third phase shift line which linearly extends and crosses the first phase shift line.

50 (Original): The phase shifter according to claim 49, wherein an area on one side and an area on the other side of the first phase shift line and the second phase shift line have a phase difference of approximately 180 degrees, and an area on one side and an area on the other side of the third phase shift line have a phase difference of approximately 180 degrees.

51 (Original): The phase shifter according to claim 49, wherein the first phase shift line and the third phase shift line are substantially orthogonal to each other.